TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

## 2SK2837

# Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance :  $R_{DS (ON)} = 0.21 \Omega (typ.)$ 

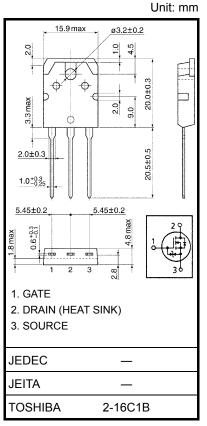
High forward transfer admittance : |Y<sub>fs</sub>| = 17 S (typ.)

• Low leakage current :  $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 500 \text{ V)}$ 

• Enhancement mode :  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

| Characteri             | stics                  | Symbol           | Rating     | Unit |
|------------------------|------------------------|------------------|------------|------|
| Drain-source voltage   |                        | $V_{DSS}$        | 500        | V    |
| Drain-gate voltage (R  | <sub>GS</sub> = 20 kΩ) | $V_{DGR}$        | 500        | V    |
| Gate-source voltage    |                        | V <sub>GSS</sub> | ±30        | V    |
| Drain current          | DC (Note 1)            | I <sub>D</sub>   | 20         | Α    |
|                        | Pulse (Note 1)         | I <sub>DP</sub>  | 80         | Α    |
| Drain power dissipatio | n (Tc = 25°C)          | PD               | 150        | W    |
| Single pulse avalanche | e energy<br>(Note 2)   | E <sub>AS</sub>  | 960        | mJ   |
| Avalanche current      |                        | I <sub>AR</sub>  | 20         | Α    |
| Repetitive avalanche   | energy (Note 3)        | E <sub>AR</sub>  | 15         | mJ   |
| Channel temperature    |                        | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature r  | ange                   | T <sub>stg</sub> | -55 to 150 | °C   |



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max   | Unit |  |
|--|------------------------|-------|------|--|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 0.833 | °C/W |  |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 50    | °C/W |  |

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 4.08 mH,  $R_{G}$  = 25  $\Omega$ ,  $I_{AR}$  = 20 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

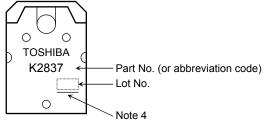
#### **Electrical Characteristics (Ta = 25°C)**

| Charac  | cteristics      | Symbol                | Test Condition   | Min | Тур. | Max  | Unit |
|---|-----------------|-----------------------|--|-----|------|------|------|
| Gate leakage cu                                 | ırrent          | I <sub>GSS</sub>      | V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V   | _   | _    | ±10  | μΑ   |
| Gate-source bre                                 | eakdown voltage | V (BR) GSS            | I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V   | ±30 | _    | _    | V    |
| Drain cut-off cu                                | rrent           | I <sub>DSS</sub>      | V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V   | _   | _    | 100  | μA   |
| Drain-source br                                 | eakdown voltage | V <sub>(BR) DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V  | 500 | _    | _    | V    |
| Gate threshold v                                | oltage/         | $V_{th}$              | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA  | 2.0 | _    | 4.0  | V    |
| Drain-source O                                  | N resistance    | R <sub>DS</sub> (ON)  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A  | _   | 0.21 | 0.27 | Ω    |
| Forward transfer                                | r admittance    | Y <sub>fs</sub>       | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A  | 10  | 17   | _    | S    |
| Input capacitano                                | e               | C <sub>iss</sub>      |  |     | 3720 | _    |      |
| Reverse transfer capacitance                    |                 | C <sub>rss</sub>      | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz   | _   | 340  | _    | pF   |
| Output capacitance                              |                 | C <sub>oss</sub>      |  |     | 1165 | _    |      |
| Switching time                                  | Rise time       | t <sub>r</sub>        | $V_{GS} \stackrel{10V}{\underset{OV}{\bigcap}} \stackrel{I_{D}=10A}{\underset{R_{L}=20\Omega}{\bigcap}} V_{OUT}$ | _   | 30   | _    | ns   |
|   | Turn-on time    | t <sub>on</sub>       |  | _   | 70   | _    |      |
|   | Fall time       | t <sub>f</sub>        |  | _   | 50   | _    |      |
|   | Turn-off time   | t <sub>off</sub>      | Duty $\leq 1\%$ , $t_{\mathbf{W}} = 10 \mu \text{s}$   |     | 290  | _    |      |
| Total gate charge (gate-source plus gate-drain) |                 | Qg                    |  |     | 80   |      |      |
| Gate-source charge                              |                 | Q <sub>gs</sub>       | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6 \text{ A}$                                       |     | 48   | _    | nC   |
| Gate-drain ("miller") Charge                    |                 | Q <sub>gd</sub>       |  |     | 32   |      |      |

#### Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _   | _   | _    | 20   | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _   | _   | _    | 80   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V |     | 540  | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dI <sub>DR</sub> / dt = 100 A / μs            |     | 5.4  | _    | μC   |

### Marking

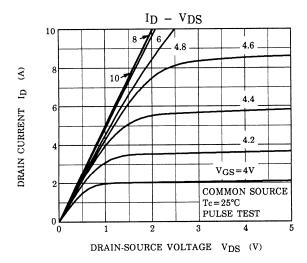


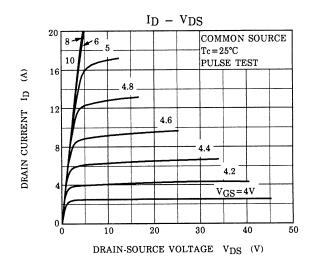
Note 4: A line under a Lot No. identifies the indication of product

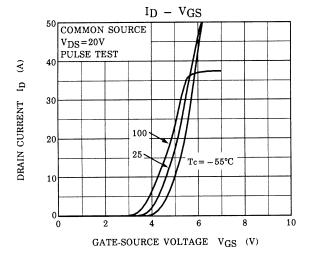
Not underlined: [[Pb]]/INCLUDES > MCV

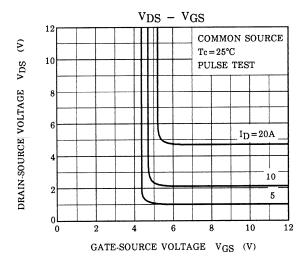
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

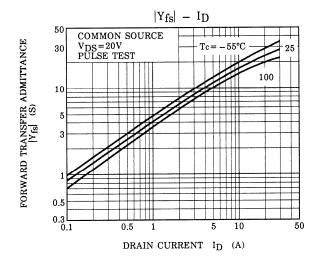
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

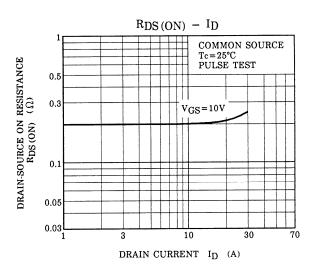




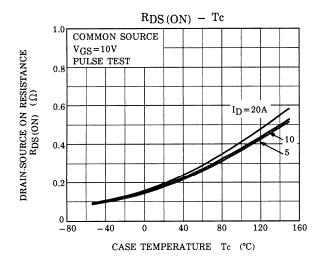


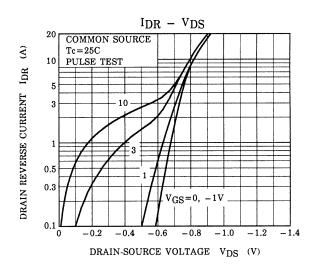


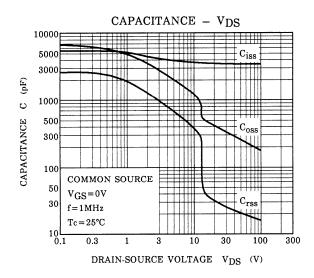


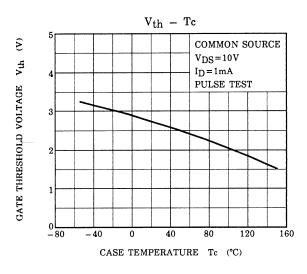


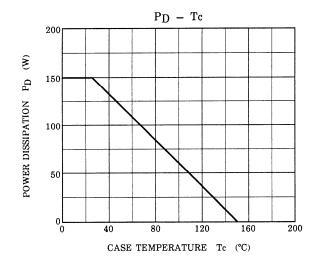
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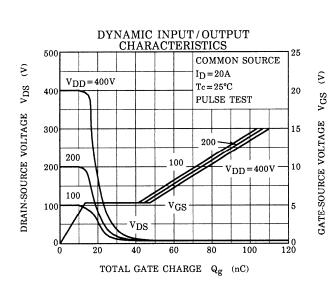


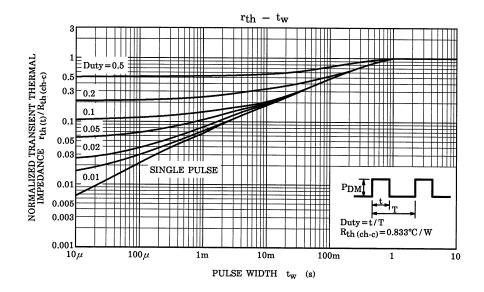


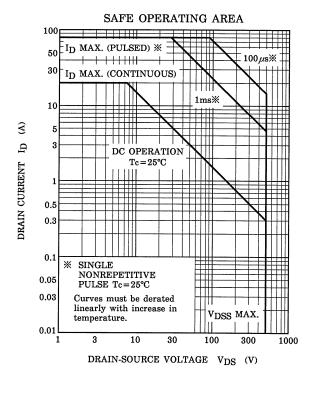


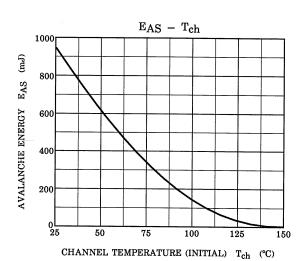


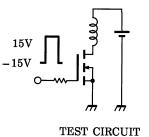


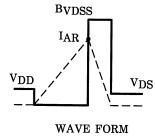












$$R_G = 25 \Omega$$
  
 $V_{DD} = 90 \text{ V}, L = 4.08 \text{ mH}$ 

$$EAS = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left( \frac{BVDSS}{BVDSS - VDD} \right)$$

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